Zibo Seno Electronic Engineering Co., Ltd.



RS601M –RS607M 🚱 📈

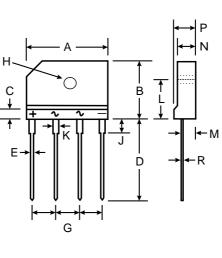
6.0A GLASS PASSIVATED BRIDGE RECTIFIER

Features

- Glass Passivated Die Construction
- High Case Dielectric Strength of 1500V_{RMS}
- Low Reverse Leakage Current
- Surge Overload Rating to 170A Peak
- Ideal for Printed Circuit Board Applications
- Plastic Material UL Flammability Classification 94V-0
- Lead Free:For RoHS / Lead Free Version

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads, Solderable per MIL-STD-202, Method 208
- Polarity: Molded on Body
- Mounting: Through Hole for #6 Screw
- Mounting Torque: 5.0 in-lbs Maximum
- Weight: 6.6 grams (approx)
- Marking: Type Number



	RS-6M							
	Dim	Min	Max					
	Α	24.80	25.20					
	В	14.70	15.30					
	С	4.00 Nominal						
Л	D	17.20	17.80					
	Е	0.90	1.10					
	G	7.30	7.70					
	Н	3.10 Ø	3.40 Ø					
	J	3.30	3.70					
	к	1.50	1.90					
	L	9.30	9.70					
	м	2.50	2.90					
	N	3.40	3.80					
	Р	4.40	4.80					
	R	0.60	0.80					
	All Dimensions in mm							

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Single phase, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	RS 601M	RS 602M	RS 603M	RS 604M	RS 605M	RS 606M	RS 607M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Forward Rectified Output Current @ T _C = 110°C		6.0							Α
Non-Repetitive Peak Forward Surge Current, 8.3 ms single half-sine-wave superimposed on rated load (JEDEC method)		170							А
Forward Voltage per element @ I _F = 3.0A	V _{FM}	1.0							V
Peak Reverse Current $@ T_C = 25^{\circ}C$ at Rated DC Blocking Voltage $@ T_C = 125^{\circ}C$		2.0 500						μA	
I ² t Rating for Fusing (t < 8.3ms) (Note 1)		120							A ² s
Typical Junction Capacitance per Element (Note 2)		55							pF
Typical Thermal Resistance Junction to Case (Note 3)		1.8							°C/W
Operating and Storage Temperature Range		-55 to +150						°C	

Notes: 1. Non-repetitive, for t > 1ms and < 8.3 ms.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC.

3. Thermal resistance from junction to case per element. Unit mounted on 75 x 75 x 1.6mm aluminum plate heat sink.

Zibo Seno Electronic Engineering Co., Ltd.

